2025년 2월 12일(수)-14일(금) | 강원도 하이원리조트

Future Normal in Semiconductor

2025-02-14(금), 09:00-10:45

좌장: 추후업데이트 예정

P. Device for Energy (Solar Cell, Power Device, Battery, etc.) 분과 [FI1-P] Power Device

초청 FI1-P-1 09:00-09:30	Gallium Nitride Power Semiconductor Devices Ho-Young Cha ^{1,2} 1Hongik University, ² CHIPSK
FI1-P-2 09:30-09:45	Enhancing BeO Electric Properties on 4H-SiC with SiO ₂ Interlayer for Power Device Applications Sangoh Han ^{1,2} , Juyoung chae ^{1,2} , Jonghyun Bae ^{1,2} , Dohwan Jung ¹ , Siwon Lee ³ , and Jungwoo Oh ^{1,2} School of Integrated Technology, Yonsei University, ² BK ²¹ Graduate Program in Intelligent Semiconductor Technology, Yonsei University, ³ Nano Science and Engineering, Yonsei University
FI1-P-3 09:45-10:00	Self-aligned 플라즈마 처리를 통한 NiO/β-Ga ₂ O ₃ 이종 접합 파워다이오드 의 질소 도핑 김동빈 ¹ , 백종수 ¹ , 최윤호 ¹ , 김형우 ² , 조병진 ¹ ¹ 한국과학기술원 전기 및 전자공학부, ² 한국전기연구원 전력반도체연구단
FI1-P-4 10:00-10:15	Eco-Friendly Power Sources for Interactive Sensor-Embedded Displays Using Transient Battery Technology Hyeonbin Jo, Mukurala Nagaraju, Geun Lee, Hyeon Hong Lee, Hanmin Kim, and Sung Hun Jin Incheon National University
FI1-P-5 10:15-10:30	Transferred graphene monolayer for β-Ga ₂ O ₃ Based Power Devices Applications Madani Labed ^{1,2} , Jang Hyeok Park ^{1,2} , You Seung Rim ^{1,2} , Bo-In Park ^{3,4} , Jekyung Kim ^{3,4} , and Jeehwan Kim ^{3,4} ¹ Department of Semiconductor Systems Engineering and Convergence Engineering for Intelligent Drone, Sejong University, ² Institute of Semiconductor and System IC, Sejong University, ³ Department of Mechanical Engineering, MIT, ⁴ Research Laboratory of Elect

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FI1-P-6 10:30-10:45 이온 주입 공정을 활용한 다이아몬드 기반 쇼트키 장벽 다이오드

김인화¹, 김효경², 김기현¹

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